

Supplementary Document

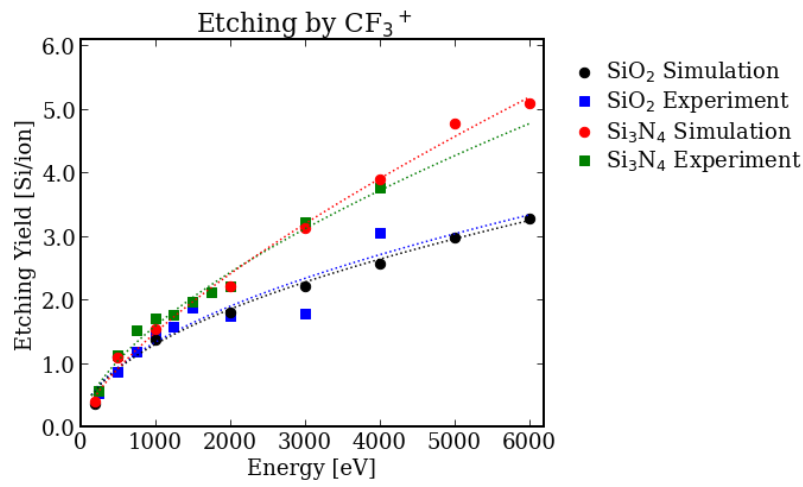


Fig.1. Comparison of the simulation and experiment etching yield of SiO_2 and Si_3N_4 by CF_3^+ ions.

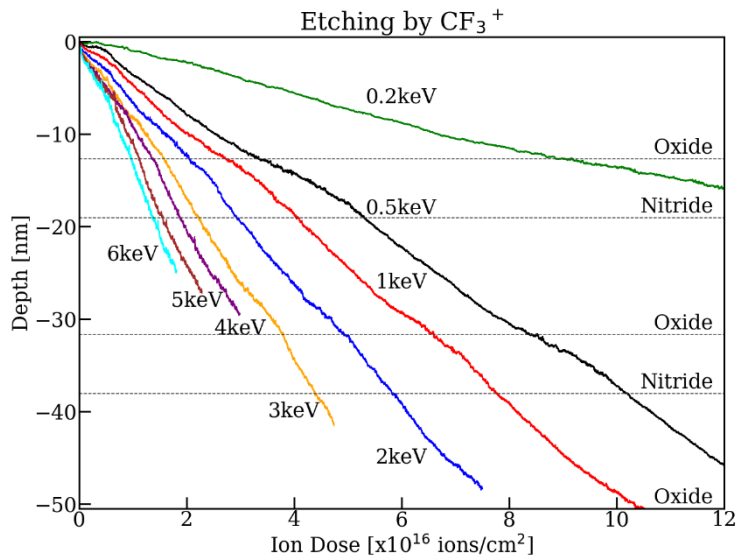


Fig. 2. Change in depth of ONO multilayer as a function of CF_3^+ ion dose.